

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.:

10/699,221

Confirmation No.:

2799

First Named Inventor:

Constantin Bulucea

Filing Date:

31 October 2003

Group Art Unit:

2814

Examiner:

Unknown

Atty. Docket No.:

NS-5127-1D US

Title:

Gate-Enhanced Junction Varactor With Gradual Capacitance

Variation

Assignee:

National Semiconductor Corporation

Mountain View, California 9 May 2005

COMMISSIONER FOR PATENTS PO Box 1450 Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97(b)

Sir:

Pursuant to 37 CFR 1.56, 1.97, and 1.98, each document listed on the accompanying substitute PTO Form 1449 is called to the attention of the Examiner for the above patent application. A copy of each listed document is enclosed.

Takeuchi et al. is cited on page 59 of the specification of the above application. U.S. Patent Application Publication US 2002/0074589 A1 (Benaissa et al.) was recently cited in parent U.S. patent application 10/054,653 during its prosecution.

Citation of each listed document shall not be construed as:

- 1. an admission that the document is necessarily prior art with respect to the instant invention;
- 2. a representation that a search has been made; or
- an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR 1.56(b).

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This information disclosure statement is submitted under the provisions of 37 CFR 1.97(b).

EXPRESS MAIL LABEL NO.:

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Respectfully submitted,

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U.S. Patent Documents										
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	AN	OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) AN Takeuchi et al, "A New Multiple Transistor Design Methodology for High Speed Low Power SOCs," IEDM								
		Technical Digest, Dec	ember 2001, pa	iges 22.6.1 - 22.6.7	1					
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.										